



Description

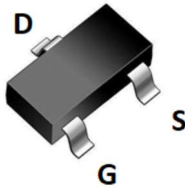
JMT N-channel Enhancement Mode Power MOSFET

Features

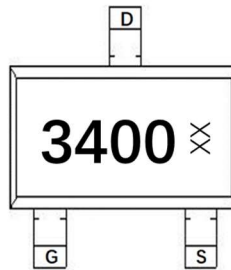
- 30V,5.8A
 $R_{DS(ON)} < 26m\Omega$ @ $V_{GS} = 10V$
 $R_{DS(ON)} < 32m\Omega$ @ $V_{GS} = 4.5V$
 $R_{DS(ON)} < 50m\Omega$ @ $V_{GS} = 2.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

Application

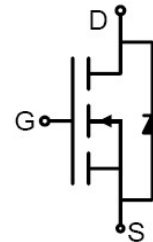
- Load Switch
- PWM Application
- Power management



SOT-23-3L top view



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
3400	JMTJ3400A	TAPING	SOT-23-3L	7inch	3000	180000

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Symbol	Parameter		Max.	Units
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		±12	V
I _D	Continuous Drain Current	T _A = 25°C	5.8	A
		T _A = 100°C	3.8	A
I _{DM}	Pulsed Drain Current ^{note1}		23.2	A
P _D	Power Dissipation	T _A = 25°C	1.36	W
R _{θJA}	Thermal Resistance, Junction to Case		92	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±12V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.5	0.9	1.4	V
R _{DS(on)}	Static Drain-Source on-Resistance note2	V _{GS} =10V, I _D =4.2A	-	19	26	mΩ
		V _{GS} =4.5V, I _D =4A	-	23	32	
		V _{GS} =2.5V, I _D =1A	-	30	50	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz	-	535	-	pF
C _{oss}	Output Capacitance		-	130	-	pF
C _{rss}	Reverse Transfer Capacitance		-	36	-	pF
Q _g	Total Gate Charge	V _{DS} =15V, I=4.2A, V _{GS} =4.5V	-	4.8	-	nC
Q _{gs}	Gate-Source Charge		-	1.2	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	1.7	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =15V, I _D =4A, R _{GEN} =3Ω, V _{GS} =4.5V	-	12	-	ns
t _r	Turn-on Rise Time		-	52	-	ns
t _{d(off)}	Turn-off Delay Time		-	17	-	ns
t _f	Turn-off Fall Time		-	10	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	5.8	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	23.2	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =5.8A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%



Typical Performance Characteristics

Figure1: Output Characteristics

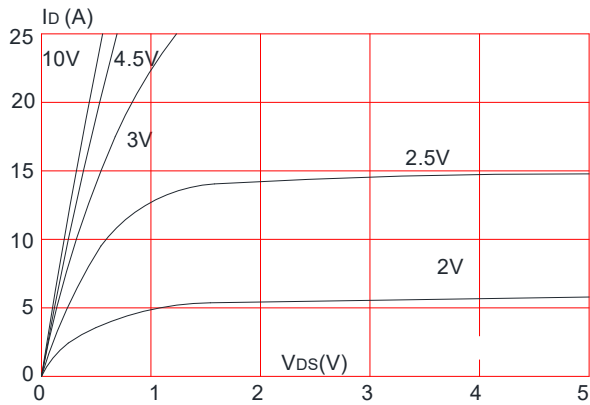


Figure 2: Typical Transfer Characteristics

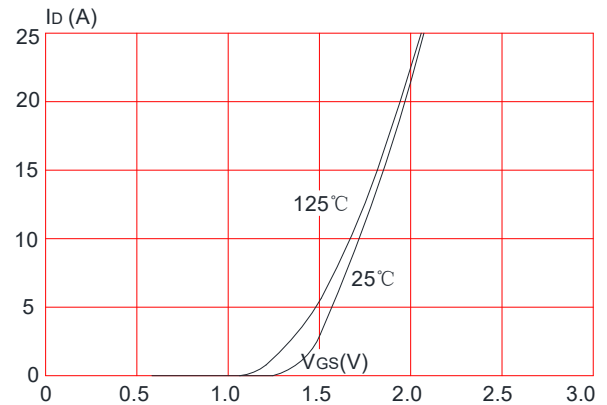


Figure 3: On-resistance vs. Drain Current

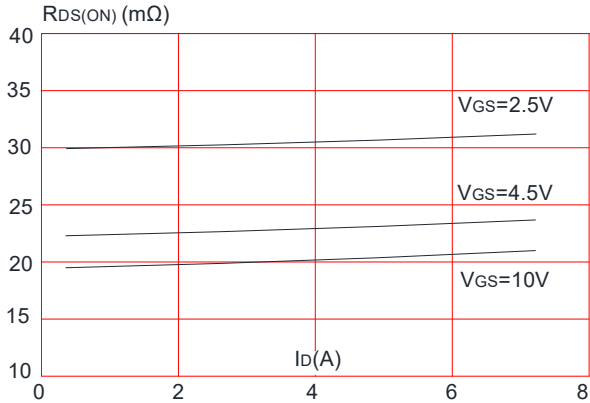


Figure 4: Body Diode Characteristics

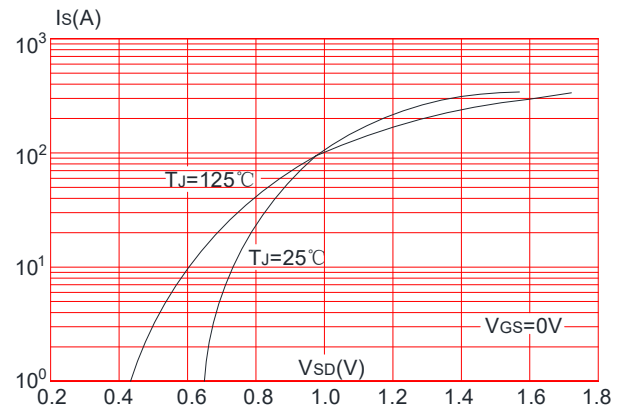


Figure 5: Gate Charge Characteristics

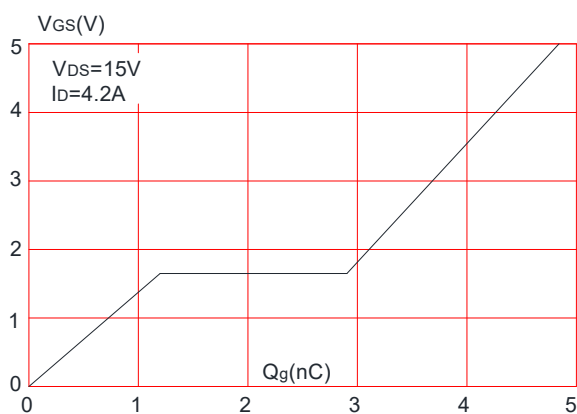


Figure 6: Capacitance Characteristics

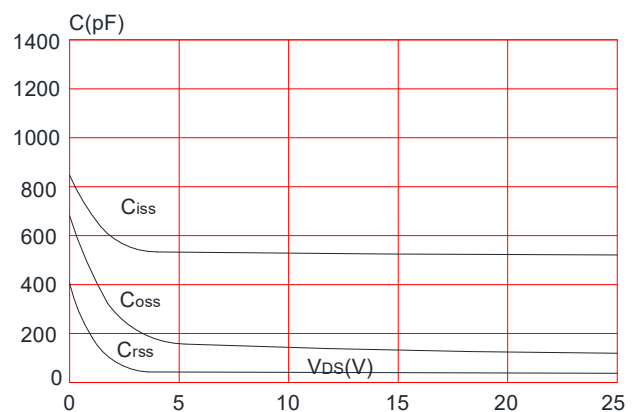


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

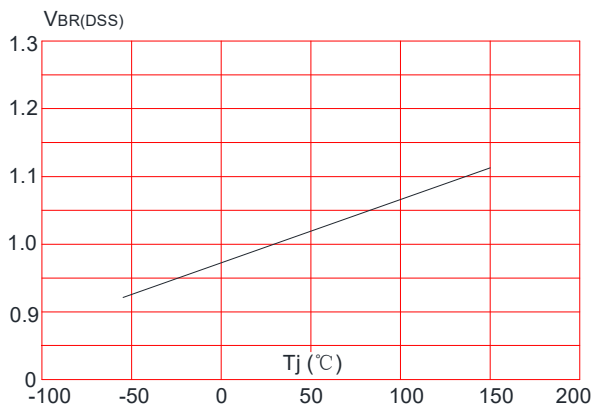


Figure 8: Normalized on Resistance vs. Junction Temperature

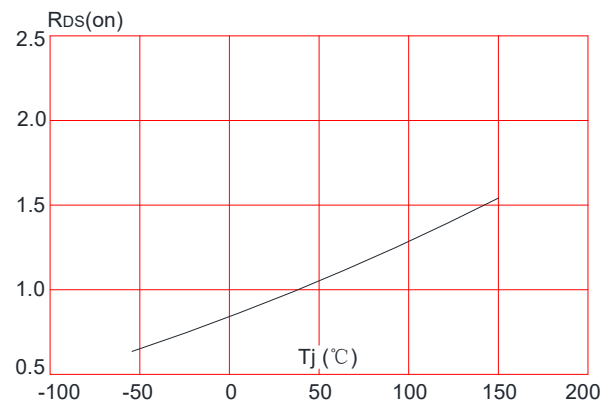


Figure 9: Maximum Safe Operating Area

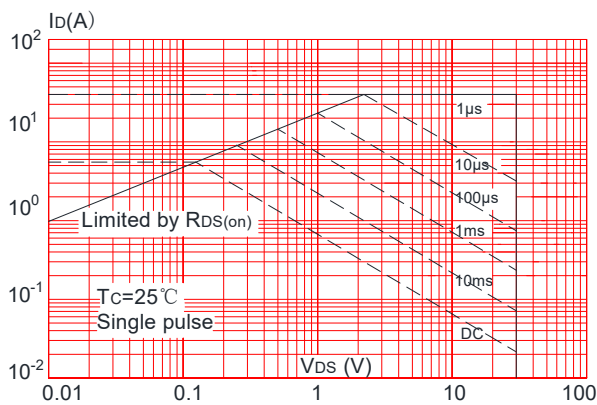


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

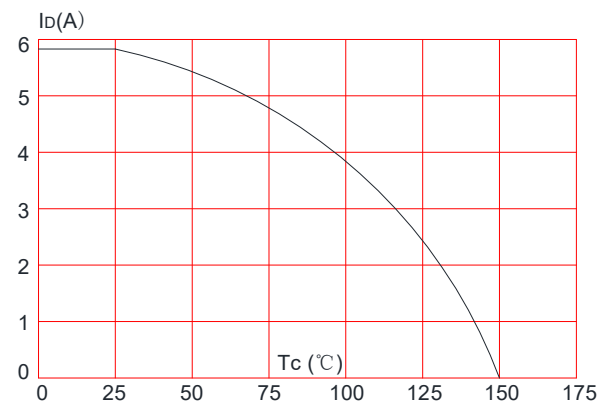
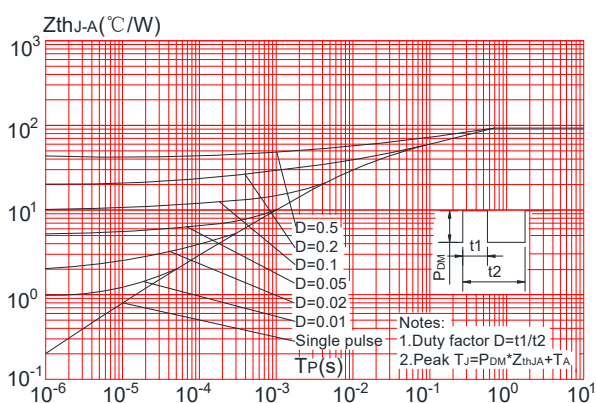


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Test Circuit

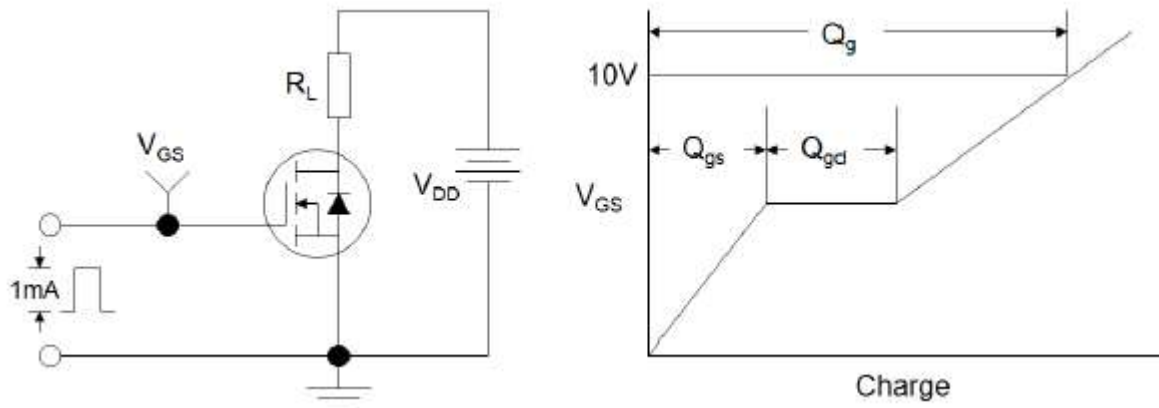


Figure1:Gate Charge Test Circuit & Waveform

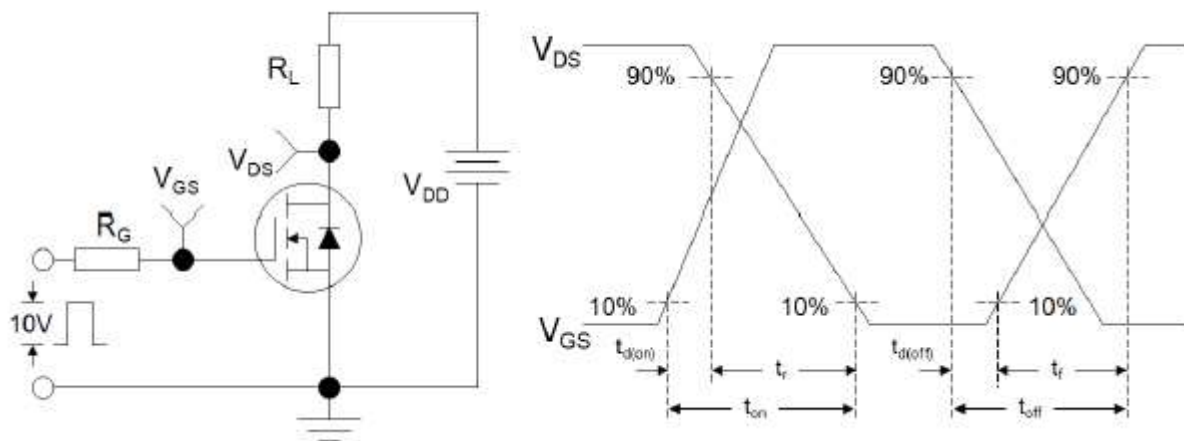


Figure 2: Resistive Switching Test Circuit & Waveforms

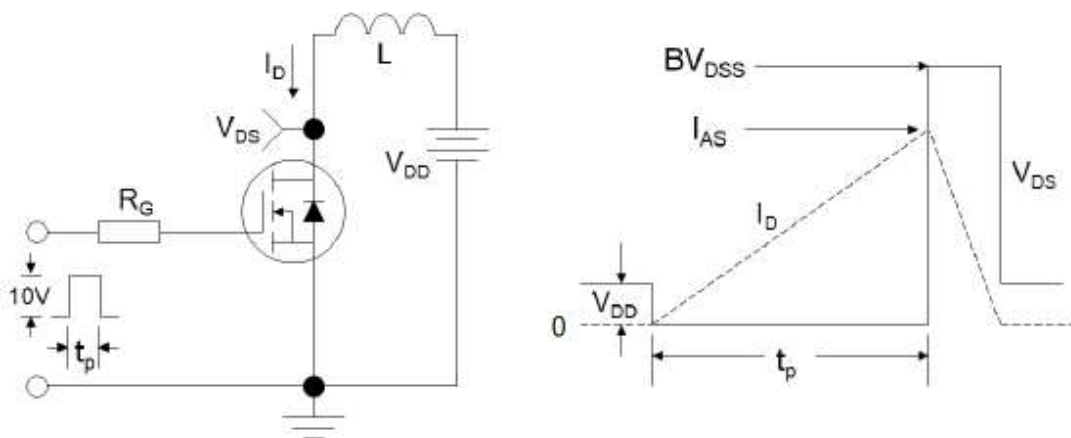
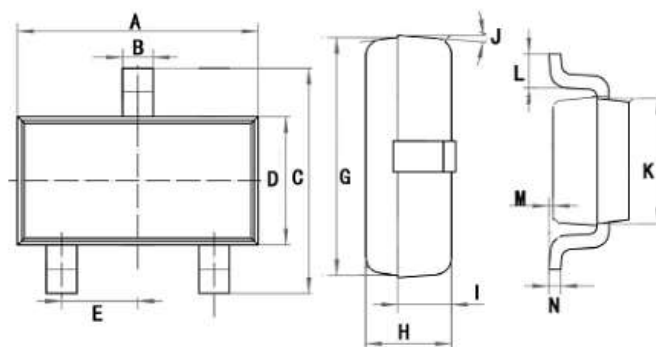


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Package Mechanical Data-SOT-23-3L



A	2.90±0.1	E	0.950	J	7°	N	0.15 ^{+0.03}
B	0.4±0.01	G	2.85±0.1	K	1.550±0.1		
C	2.80±0.20	H	1.10±0.1	L	0.40		
D	1.60±0.1	I	0.70±0.1	M	0.05±0.03		

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